

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	60	V
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ			V _{DGR}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
				±40	
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	170	mA
		T _A = +85°C		120	
		T _A = +100°C		105	
Continuous Drain Current (Note 7) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	210	mA
		T _A = +85°C		150	
		T _A = +100°C		135	
Maximum Continuous Body Diode Forward Current (Note 7)			I _S	0.5	A
Pulsed				2	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation	(Note 6)	P _D	370	mW
	(Note 7)		540	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	348	°C/W
	(Note 7)		241	
Thermal Resistance, Junction to Case	(Note 7)	R _{θJC}	91	°C
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	70	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	V _{DS} = 60V, V _{GS} = 0V
				@ T _C = +125°C		
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.2	7.5	Ω	V _{GS} = 5.0V, I _D = 0.05A
			@ T _J = +25°C	—		5.0
			@ T _J = +125°C	4.4		13.5
On-State Drain Current	I _{D(ON)}	0.5	1.0	—	A	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance	g _{FS}	80	—	—	mS	V _{DS} = 10V, I _D = 0.2A
Diode Forward Voltage	V _{SD}	—	0.78	1.5	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	22	50	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{OSS}	—	11	25	pF	
Reverse Transfer Capacitance	C _{RSS}	—	2.0	5.0	pF	
Gate Resistance	R _g	—	120	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	223	—	pC	V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	—	82	—		
Gate-Drain Charge	Q _{gd}	—	178	—		
SWITCHING CHARACTERISTICS (Note 9)						
Turn-On Delay Time	t _{D(ON)}	—	2.8	—	ns	V _{DD} = 30V, I _D = 0.2A, R _L = 150Ω, V _{GEN} = 10V, R _{GEN} = 25Ω
Turn-On Rise Time	t _r	—	3.0	—		
Turn-Off Delay Time	t _{D(OFF)}	—	7.6	—		
Turn-Off Fall Time	t _f	—	5.6	—		

- Notes:
6. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 7. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

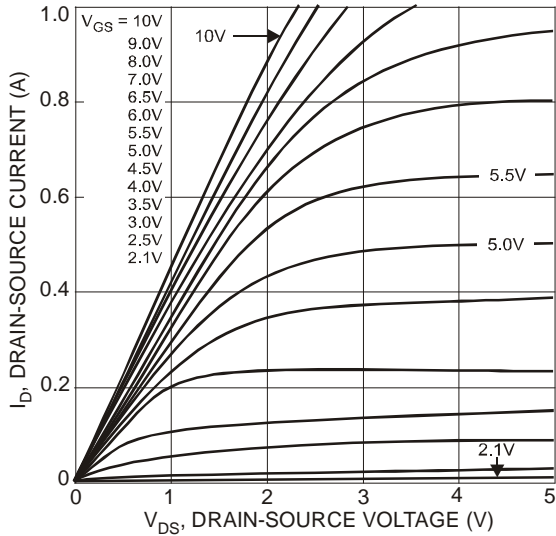


Fig. 1 On-Region Characteristics

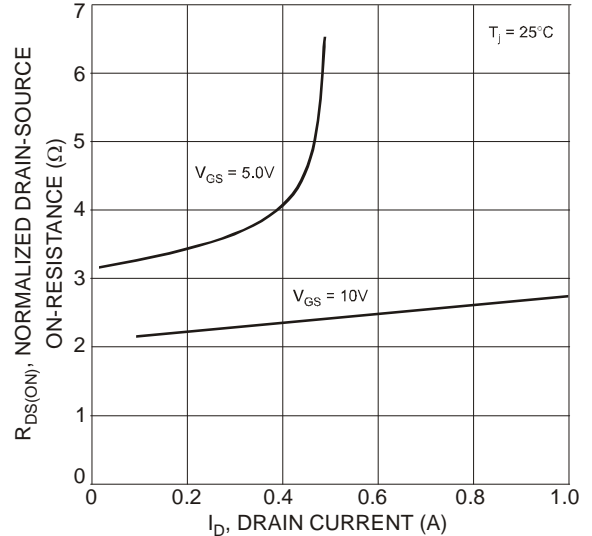


Fig. 2 On-Resistance vs. Drain Current

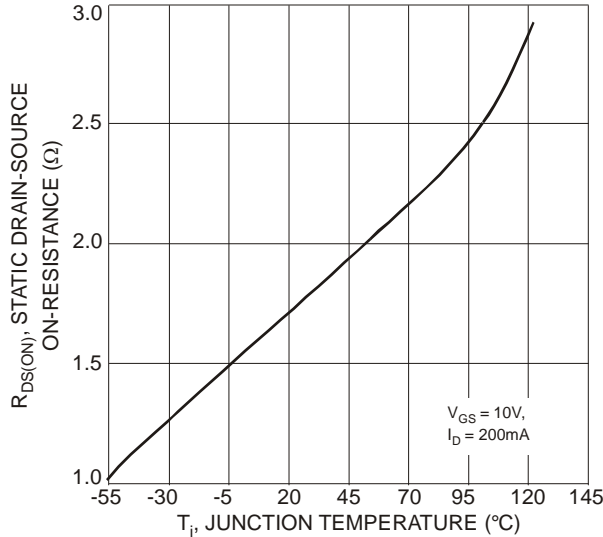


Fig. 3 On-Resistance vs. Junction Temperature

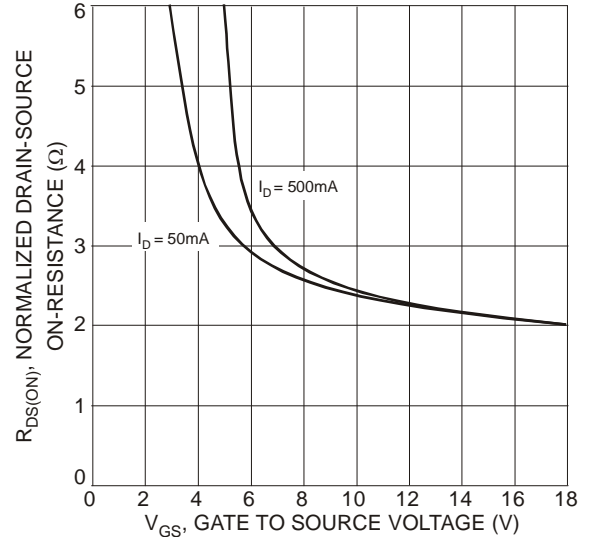


Fig. 4 On-Resistance vs. Gate-Source Voltage

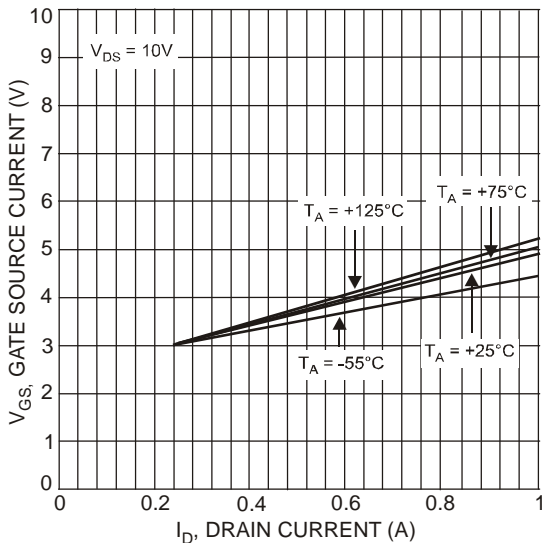


Fig. 5 Typical Transfer Characteristics

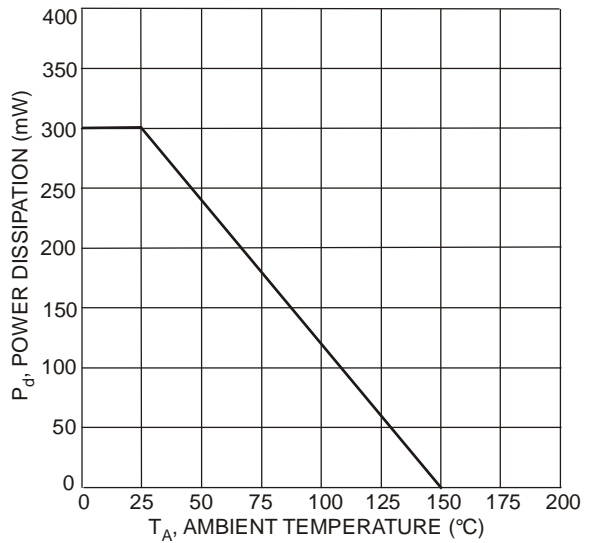
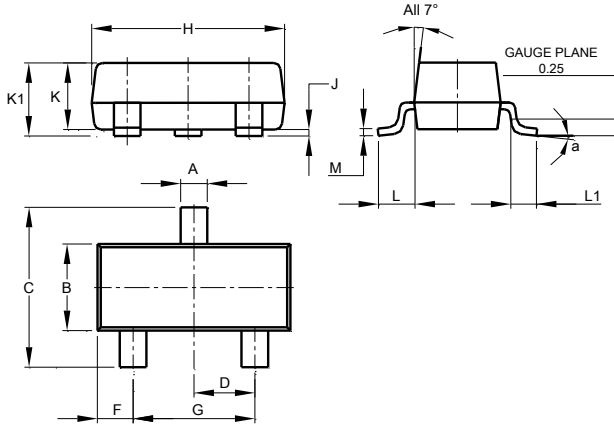


Fig. 6 Max Power Dissipation vs. Ambient Temperature

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

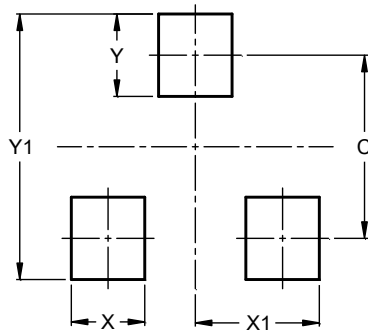


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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